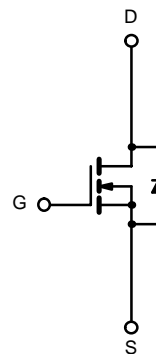
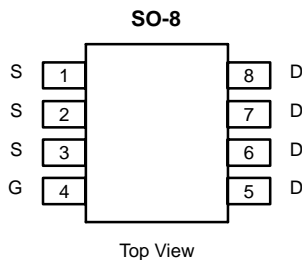




## N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
200	0.080 @ V <sub>GS</sub> = 10 V	4.0
	0.090 @ V <sub>GS</sub> = 6.0 V	3.8

**TrenchFET<sup>®</sup>**  
Power MOSFETs



Ordering Information: Si4490DY  
Si4490DY-T1 (with Tape and Reel)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	V <sub>DS</sub>	200		V	
Gate-Source Voltage	V <sub>GS</sub>	± 20			
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	4.0	2.85	A
		T <sub>A</sub> = 70 °C	3.2	2.3	
Pulsed Drain Current	I <sub>DM</sub>	40			
Avalanch Current	I <sub>AS</sub>	15			
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	2.6	1.3		
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	3.1	1.56	W
		T <sub>A</sub> = 70 °C	2.0	1.0	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 10 sec	33	40	°C/W
		Steady State	65	80	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	17	21		

Notes

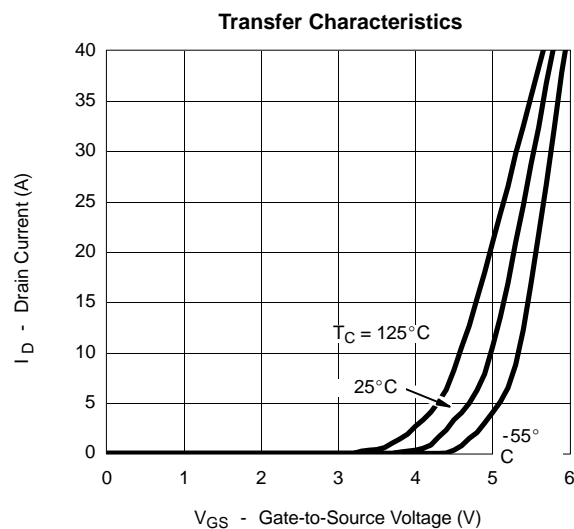
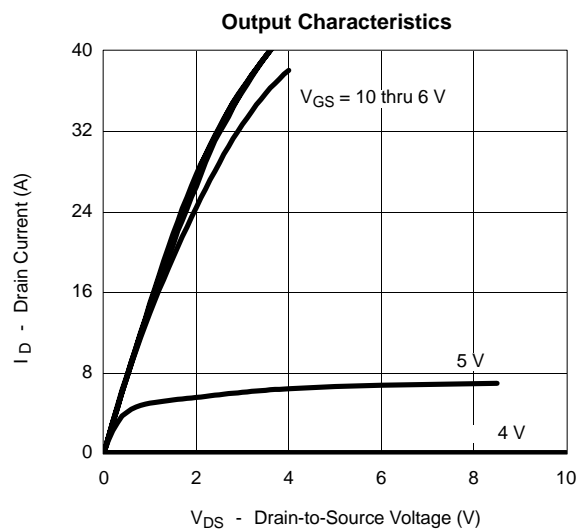
a. Surface Mounted on 1" x 1" FR4 Board.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C			5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	40			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.0 A		0.065	0.080	Ω
		V <sub>GS</sub> = 6.0 V, I <sub>D</sub> = 4.0 A		0.070	0.090	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5 A		19		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2.8 A, V <sub>GS</sub> = 0 V		0.75	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.0 A		34	42	nC
Gate-Source Charge	Q <sub>gs</sub>			7.5		
Gate-Drain Charge	Q <sub>gd</sub>			12.0		
Gate Resistance	R <sub>g</sub>		0.2	0.85	1.3	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 25 Ω I <sub>D</sub> = 4.0 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω		14	20	ns
Rise Time	t <sub>r</sub>			20	30	
Turn-Off Delay Time	t <sub>d(off)</sub>			32	50	
Fall Time	t <sub>f</sub>			25	35	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.8 A, di/dt = 100 A/μs		70	100	

## Notes

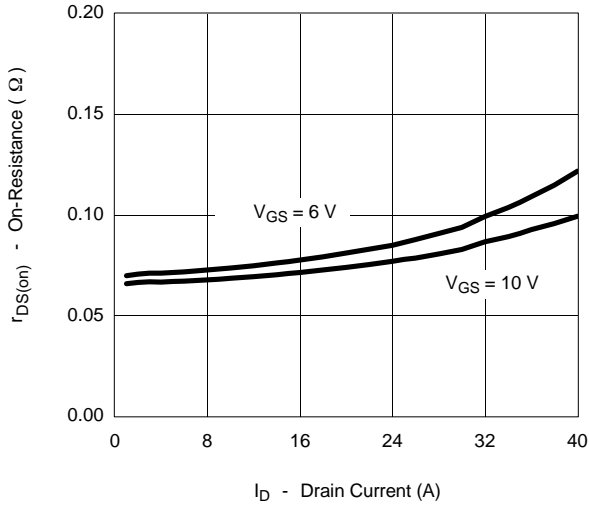
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

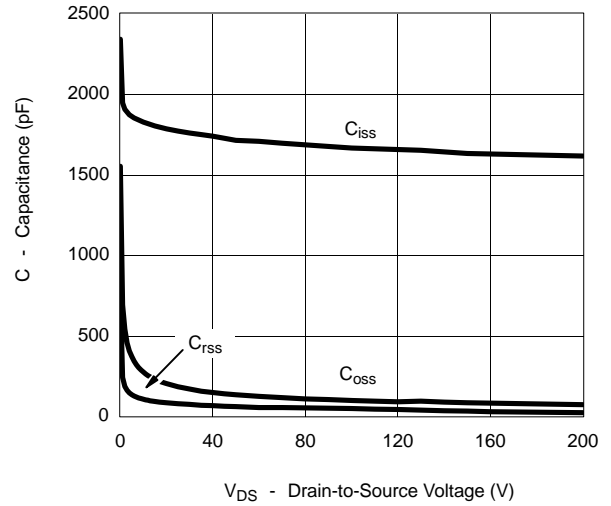


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

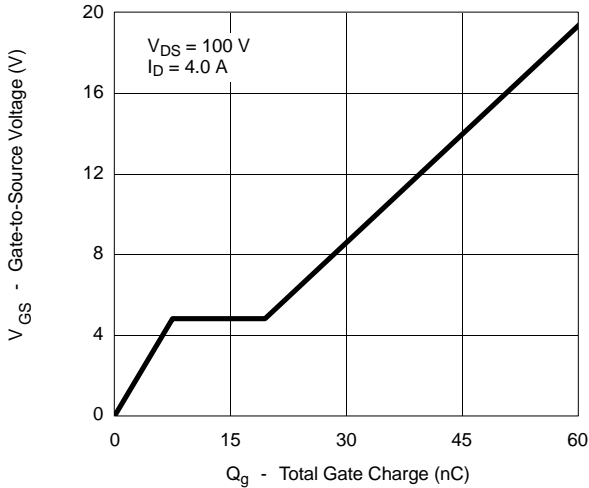
**On-Resistance vs. Drain Current**



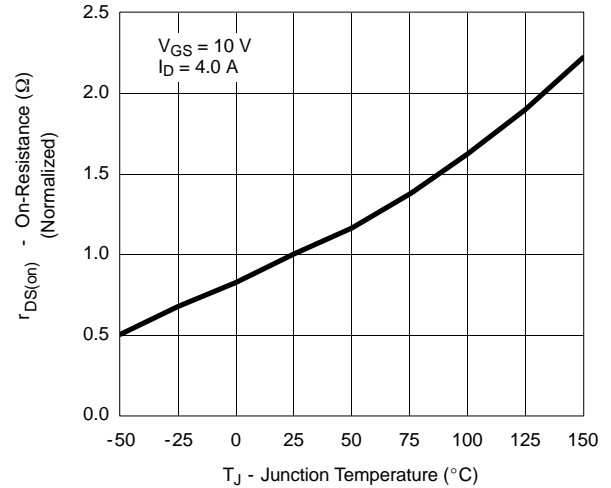
**Capacitance**



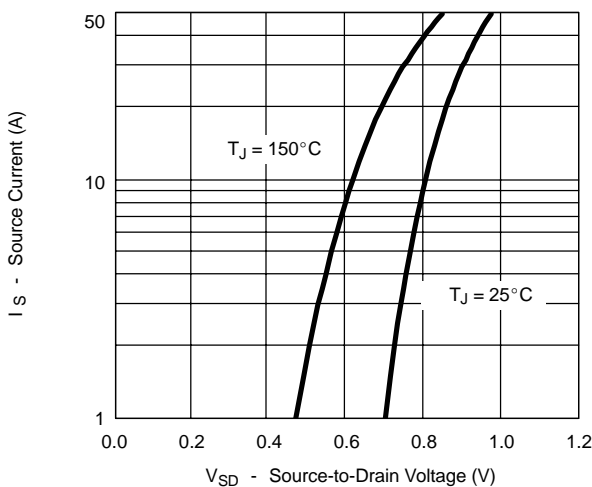
**Gate Charge**



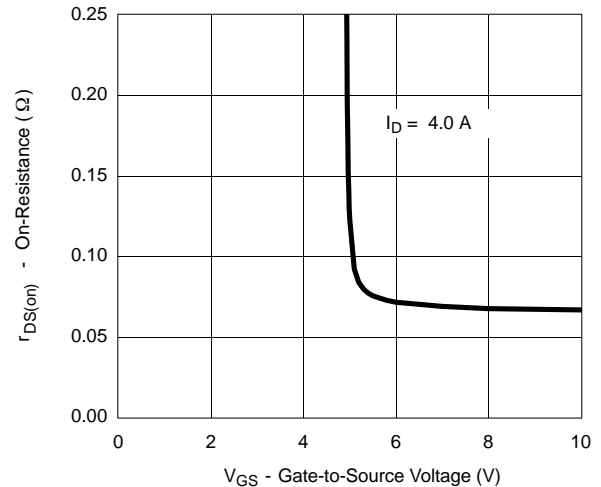
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

